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Am27LV010/Am27LV010B

1 Megabit (131,072 x 8-Bit) Low Voltage CMOS EPROM

Advanced Micro Devices

DISTINCTIVE CHARACTERISTICS

- Single +3.3 V power supply
 - Regulated power supply 3.0 V-3.6 V
 - Unregulated power supply 2.7 V-3.6 V (for battery operated systems)
- Low power consumption:
 - 10 μA typical CMOS standby current
 - 30 μW typical standby power
 - 20 mW typical power at 5 MHz
- Fast access time—100 ns
- JEDEC-approved pinout
 - Pin compatible with 5.0 V 1 Mbit EPROM
 - Easy upgrade from 28-pin EPROMs

- Fast Flashrite programming
 - Typical programming time of 16 seconds
- Latch-up protected to 100 mA from -1 V to Vcc +1 V
- High noise immunity
- Compact 32-pin DIP, PDIP, PLCC, and TSOP packages
- Versatile features for simple interfacing
 - Both CMOS and TTL input/output compatibility
 - Two line control functions

GENERAL DESCRIPTION

The Am27LV010 is a low voltage, low power 1 Mbit, ultraviolet erasable, progammable read-only memory, organized as 128K words by 8 bits per word.

The Am27LV010 operates from a single power supply of 3.3 V and is offered with two power supply tolerances. The Am27LV010 has a Vcc tolerance range of 3.3 V \pm 0.3 V making it suitable for use in systems that have regulated power supplies. The Am27LV010B has a voltage supply range of 2.7 V–3.6 V making it an ideal part for battery operated systems.

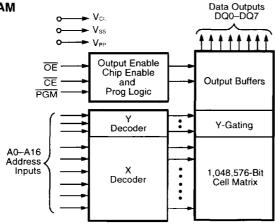
Maximum power consumption of the Am27LV010 in standby mode is only 90 μ W. If the device is constantly accessed at 5 MHz, then the maximum power consumption increases to 54 mW. These power ratings are significantly lower than typical EPROMs. Also, as power consumption is proportional to voltage squared, 3.3 V

devices consume at least 57% less power than their 5.0 V counterparts. Due to its lower current and voltage, the Am27LV010 is well-suited for battery operated and portable systems as it extends the battery life in these systems. Typical applications are notebook and handheld computers as well as cellular phones.

The Am27LV010 is packaged in the industry standard 32-pin windowed ceramic DIP packages, as well as one-time programmable (OTP) packages. This device is pin-compatible with the 5.0 V devices.

The Am27LV010 uses AMD's Flashrite programming algorithm (100 μs pulses) resulting in typical programming time of 16 seconds. This device is manufactured on AMD's sub-micron process technology which provides high speed, low power and high noise immunity.

BLOCK DIAGRAM



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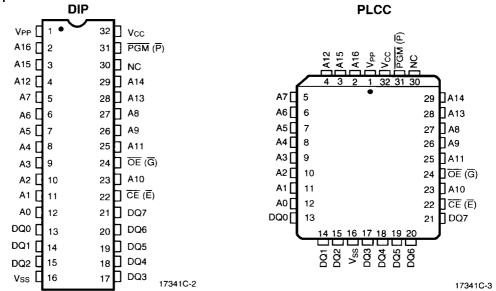
Publication# 17341 Rev. C Amendment/0 Issue Date: May 1995

PRODUCT SELECTOR GUIDE

Family Part No		Am27LV010/Am27LV010B									
Ordering Part No: Am27LV010 (3.0 V – 3.6 V)	-100	-120	-150	-200	-250	-300					
Am27LV010B (2.7 V - 3.6 V)		-120	-150	-200	-250	-300					
Max Access Time (ns)	100	120	150	200	250	300					
CE (E) Access (ns)	100	120	150	200	250	300					
OE (G) Access (ns)	50	50	65	75	100	120					

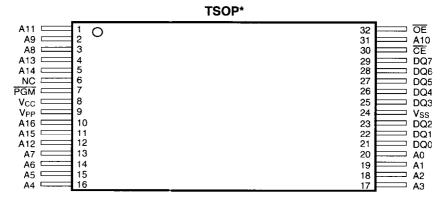
CONNECTION DIAGRAMS

Top View



Note:

1. JEDEC nomenclature is in parentheses.



Standard Pinout

17341C-4

^{*}Contact local AMD sales office for package availability.



PIN DESCRIPTION

A0-A16 = Address Inputs

 $\overline{CE}(\overline{E})$ = Chip Enable Input

DQ0-DQ7 = Data Input/Outputs

NC = No Internal Connection

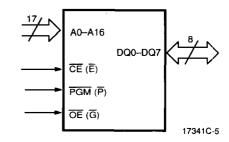
 $\overline{OE}(\overline{G})$ = Output Enable Input

 \overline{PGM} (\overline{P}) = Program Enable Input

V_{CC} = V_{CC} Supply Voltage V_{PP} = Program Voltage Input

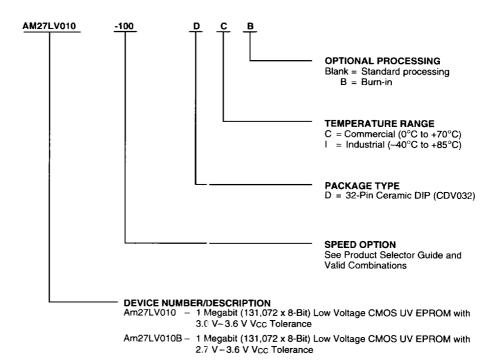
Vss = Ground

LOGIC SYMBOL



ORDERING INFORMATION UV EPROM Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of:



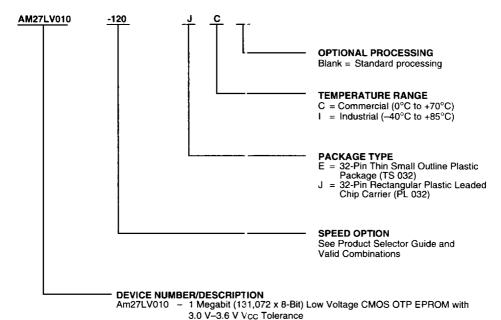
Valid Combinations								
AM27LV010-100	DC DCB							
AM27LV010-120	DC, DCB							
AM27LV010-150								
AM27LV010-200								
AM27LV010-250								
AM27LV010-300	DC, DCB,							
AM27LV010B-120	DI, DIB							
AM27LV010B-150								
AM27LV010B-200								
AM27LV010B-250								
AM27LV010B-300								

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations and to check on newly released combinations.

ORDERING INFORMATION OTP Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of:



Am27LV010B -	1 Megabit (131,072 x 8-Bit) Low Voltage CMOS OTP EPROM with
	2.7 V-3.6 V Vcc Tolerance

Valid Combinations							
AM27LV010-120							
AM27LV010-150							
AM27LV010-200							
AM27LV010-250							
AM27LV010-300	JC, EC, JI, EI						
AM27LV010B-150							
AM27LV010B-200							
AM27LV010B-250							
AM27LV010B-300							

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations and to check on newly released combinations.

FUNCTIONAL DESCRIPTION Erasing the Am27LV010

In order to clear all locations of their programmed contents, it is necessary to expose the Am27LV010 to an ultraviolet light source. A dosage of 15 W seconds/cm² is required to completely erase an Am27LV010. This dosage can be obtained by exposure to an ultraviolet lamp — wavelength of 2537 Å — with intensity of 12,000 $\mu\text{W}/\text{cm}^2$ for 15 to 20 minutes. The Am27LV010 should be directly under and about one inch from the source and all filters should be removed from the UV light source prior to erasure.

It is important to note that the Am27LV010, and similar devices, will erase with light sources having wavelengths shorter than 4000 Å. Although erasure times will be much longer than with UV sources at 2537 Å, nevertheless the exposure to fluorescent light and sunlight will eventually erase the Am27LV010 and exposure to them should be prevented to realize max mum system reliability. If used in such an environment, the package window should be covered by an opaque label or substance.

Programming the Am27LV010

Upon delivery, or after each erasure, the Am27LV010 has all 1,048,576 bits in the "ONE", or HIGH state. "ZEROs" are loaded into the Am27LV010 through the procedure of programming.

The programming mode is entered wher 12.75 V ± 0.25 V is applied to the V_{PP} pin, \overline{CE} and \overline{PGM} are at V_{IL} and \overline{OE} is at V_{IH}.

For programming, the data to be programmed is applied 8 bits in parallel to the data output pins.

The Flashrite programming algorithm reduces programming time by using initial 100 µs pulses followed by a byte verification to determine whether the byte has been successfully programmed. If the data does not verify, an additional pulse is applied for a maximum of 25 pulses. This process is repeated while sequencing through each address of the EPROM.

The Flashrite programming algorithm programs and verifies at $V_{CC} = 6.25 \, V$ and $V_{PP} = 12.75 \, V$. After the final address is completed, all bytes are compared to the original data with $V_{CC} = V_{PP} = 5.25 \, V$. Am27I V010 can be programmed using the same algorithm as the 5 V counterpart Am27C010.

Please refer to Section 6 for programming flow chart and characteristics.

Program Inhibit

Programming of multiple Am27LV010s in parallel with different data is also easily accomplished. Except for \overline{CE} , all like inputs of the parallel Am27LV010 may be

common. A TTL low-level program pulse applied to an Am27LV010 \overline{CE} input with V_{PP} = 12.75 \pm 0.25 V, \overline{PGM} LOW, and \overline{OE} HIGH will program that Am27LV010. A high-level \overline{CE} input inhibits the other Am27LV010s from being programmed.

Program Verify

A verify should be performed on the programmed bits to determine that they were correctly programmed. The verify should be performed with \overrightarrow{OE} and \overrightarrow{CE} at V_{IL} , \overrightarrow{PGM} at V_{IH} , and V_{PP} between 12.5 V and 13.0 V.

Auto Select Mode

The auto select mode allows the reading out of a binary code from an EPROM that will identify its manufacturer and type. This mode is intended for use by programming equipment for the purpose of automatically matching the device to be programmed with its corresponding programming algorithm. This mode is functional in the $25^{\circ}\text{C} \pm 5^{\circ}\text{C}$ ambient temperature range that is required when programming the Am27LV010.

To activate this mode, the programming equipment must force 12.0 \pm 0.5 V on address line A9 of the Am27LV010. Two identifier bytes may then be sequenced from the device outputs by toggling address line A0 from V $_{IL}$ to V $_{IH}$. All other address lines must be held at V $_{IL}$ during auto select mode.

Byte 0 (A0 = V_{IL}) represents the manufacturer code, and Byte 1 (A0 = V_{IH}), the device identifier code. For the Am27LV010, these two identifier bytes are given in the Mode Select table. All identifiers for manufacturer and device codes will possess odd parity, with the MSB (DQ7) defined as the parity bit.

Read Mode

The Am27LV010 has two control functions, both of which must be logically satisfied in order to obtain data at the outputs. Chip Enable (\overline{CE}) is the power control and should be used for device selection. Output Enable (\overline{OE}) is the output control and should be used to gate data to the output pins, independent of device selection. Assuming that addresses are stable, address access time (t_{ACC}) is equal to the delay from \overline{CE} to output (t_{CE}) . Data is available at the outputs t_{OE} after the falling edge of \overline{OE} , assuming that \overline{CE} has been LOW and addresses have been stable for at least t_{ACC} — t_{OE} .

Standby Mode

The Am27LV010 has a CMOS standby mode which reduces the maximum V_{CC} current to 25 $\mu A.$ It is placed in CMOS-standby when \overline{CE} is at $V_{CC}\pm0.3$ V. The Am27LV010 also has a TTL-standby mode which reduces the maximum V_{CC} current to 0.6 mA. It is placed in TTL-standby when \overline{CE} is at $V_{IH}.$ When in standby mode, the outputs are in a high-impedance state, independent of the \overline{OE} input.



Mixed Power Supply System

Am27LV010 (in 3.0 V to 3.6 V regulated power supply) can be interfaced with 5 V system only when the I/O pins (DQ0–DQ7) are not driven by the 5 V system. $V_{\text{IHmax}} = V_{\text{CCLV}} + 2.2$ V for address and clock pins and $V_{\text{IHmax}} = V_{\text{CCLV}} + 0.5$ V for I/O pins should be followed to avoid CMOS latch-up condition.

Output OR-Tieing

To accommodate multiple memory connections, a twoline control function is provided to allow for:

- Low memory power dissipation
- Assurance that output bus contention will not occur

It is recommended that \overline{CE} be decoded and used as the primary device-selecting function, while \overline{OE} be made a common connection to all devices in the array and connected to the READ line from the system control bus. This assures that all deselected memory devices are in

their low-power standby mode and that the output pins are only active when data is desired from a particular memory device.

System Applications

During the switch between active and standby conditions, transient current peaks are produced on the rising and falling edges of Chip Enable. The magnitude of these transient current peaks is dependent on the output capacitance loading of the device. At a minimum, a 0.1 μF ceramic capacitor (high frequency, low inherent inductance) should be used on each device between Vcc and Vss to minimize transient effects. In addition, to overcome the voltage drop caused by the inductive effects of the printed circuit board traces on EPROM arrays, a 4.7 μF bulk electrolytic capacitor should be used between Vcc and Vss for each eight devices. The location of the capacitor should be close to where the power supply is connected to the array.

MODE SELECT TABLE

				T	T				
Mode	Pins	CE	ŌĒ	PGM	A 0	A9	Vpp	Outputs	
Read		ViL	VIL	Х	Х	Х	X	Dout	
Output Disable		X	ViH	Х	Х	Х	Х	High Z	
Standby (TTL)		ViH		Х	Х	Х	Х	High Z	
Standby (CM	OS)	Vcc ± 0.3 V	×	Х	X	Х	×	High Z	
Program		VIL	V _{IH}	VIL	Х	Х	VPP	DIN	
Program Veri	ify	VIL	VIL	ViH	Х	Х	VPP	Dout	
Program Inhibit		ViH	X	Х	Х	Х	Vpp	High Z	
Auto Select	Manufacturer Code	VIL	VIL	Х	VIL	Vн	Х	01H	
(Note 3)	Device Code	VIL	VIL	Х	ViH	Vн	X	0EH	

Notes:

- 1. $VH = 12.0 V \pm 0.5 V$
- 2. $X = V_{IH} \text{ or } V_{II}$
- 3. A1-A8 = A10-A16 = VIL
- 4. See DC Programming Characteristics for VPP voltage during programming.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature: OTP Products -65°C to +125°C All Other Products -65°C to +150°C
Ambient Temperature with Power Applied –55°C to +125°C
Voltage with Respect to Vss: All pins except A9, Vpp, and
Vcc (Note 1)0.6 V to Vcc + 0.6 V
A9 and V _{PP} (Note 2)0.6 \ to 13.5 V
Vcc

Notes:

- During transitions, the input may overshoot V_{.S} to -2.0 V for periods of up to 20 ns. Maximum DC voltage on input and I/O may overshoot to V_{CC} + 2.0 V for periods up to 20 ns.
- During transitions, A9 and V_{PP} may overst oot V_{SS} to -2.0 V for periods of up to 20 ns. A9 and V_{PP} must not exceed 13.5 V for any period of time.

Stresses above those listed under Absolute Maximum Ratings may cause permanent device failure. This is a stress rating only; functional operation of the devices at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.

OPERATING RANGES

Ambient Temperature (T _A)	0°C to +70°C
Industrial (I) Devices Ambient Temperature (T _A)	40°C to +85°C
Supply Read Voltages:	
Vcc for Am27LV010	+3.0 V to +3.6 V
Vcc for Am27LV010B	+2.7 V to +3.6 V

Operating ranges define those limits between which the functionality of the device is guaranteed.



DC CHARACTERISTICS over operating ranges unless otherwise specified (Notes 1, 2, 3, and 4)

Parameter Symbol	Parameter Description	Test Cond	ditions	Min	Max	Unit
TTL and CM	IOS Inputs for Am27LV010 (Vcc	= 3.0 V to 3.6	V)			
Vон	Output HIGH Voltage	loн = -2.0	mA	2.4		V
Vol	Output LOW Voltage	loL = 2.0 f	m A		0.4	٧
ViH	Input HIGH Voltage			2.0	Vcc + 0.3	٧
VIL	Input LOW Voltage			-0.3	+0.8	٧
lu	Input Load Current	VIN = 0 V	to Vcc		1.0	μA
lLO	Output Leakage Current	Vout = 0	V to Vcc		5	μA
Icc ₁	Vcc Active Current (Note 3)	CE = VIL, f = 5 MH2 lout = 0 m (Open Ou			15	mA
lcc2	Vcc TTL Standby Current	CE = VIH			0.6	mA
loga	Vcc CMOS Standby Current	CE = Vcc	± 0.3 V		25	μА
IPP1	VPP Current During Read	CE = OE	= VIL, VPP = VCC		1.0	μA

Parameter Symbol	Parameter Description	Test Con	ditions	Min	Max	Unit
CMOS Input	s for Am27LV010B (Vcc = 2.7 V t	o 3.6 V)				
Vон	Output HIGH Voltage	Юн = −20		Vcc - 0.1		V
		Іон = −10	0 μΑ	Vcc - 0.2		>
Vol	Output LOW Voltage	lot = 20 i	Α		0.1	V
		loL = 100	μΑ		0.2	٧
ViH	Input HIGH Voltage			2.0	Vcc + 0.3	V
ViL	Input LOW Voltage			-0.3	0.8	٧
ILI	Input Load Current	VIN = 0 V	to +Vcc		1.0	μА
ILO	Output Leakage Current	Vout = 0	V to +Vcc		5	μA
Icc1	Vcc Active Current (Note 3)	CE = VIL, f = 5 MH2 lout = 0 to (Open Out	n A		15	mA
ICC2	Vcc TTL Standby Current	CE = ViH			0.6	mA
lcc3	Vcc CMOS Standby Current	CE = Vcc	± 0.3 V		25	μA
IPP1	VPP Current During Read	CE = OE	= VIL, VPP = VCC		1.0	μА

Notes:

- 1. V_{CC} must be applied simultaneously or before V_{PP}, and removed simultaneously or after V_{PP}.
- 2. Caution: The Am27LV010 must not be removed from (or inserted into) a socket when V_{CC} or V_{PP} is applied.
- 3. I_{CC1} is tested with $\overline{OE} = V_{IH}$ to simulate open outputs.
- 4. Minimum DC Input Voltage is -0.3 V. During transitions, the inputs may overshoot to -2.0 V for periods less than 20 ns. Maximum DC Voltage on output pins is $V_{CC} + 0.3$ V, which may overshoot to $V_{CC} + 2.0$ V for periods less than 20 ns.

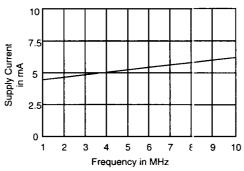


Figure 1. Typical Supply Current vs. Frequency Vcc = 3.6 V, T = 25°C

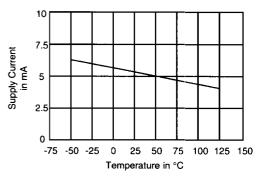


Figure 2. Typical Supply Current vs. Temperature Vcc = 3.6 V, f = 5 MHz

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CAPACITANCE

Parameter			CDV	CDV032		CDV032 PL 032		TS 032		
Symbol	Parameter Description	Test Conditions	Тур	Max	Тур	Max	Тур	Max	Unit	
Cin	Input Capacitance	Viri = 0 V	10	12	8	10	10	12	pF	
Соит	Output Capacitance	Vout = 0 V	12	15	9	12	12	14	pF	

Notes:

- 1. This parameter is only sampled and not 100% tested.
- 2. $T_A = +25^{\circ}C$, f = 1 MHz.



SWITCHING CHARACTERISTICS over operating ranges unless otherwise specified (Notes 1, 3, and 4)

					Am27LV010/Am27LV010B						
JEDEC	Standard	Parameter Description	Test Conditions		-100	-120	-150	-200	-250	-300	Unit
tavqv	tacc	Address to Output Delay	CE = OE =VII	Min Max	- 100	120	- 150	200	 250	- 300	ns
tELQV	t CE	Chip Enable	ŌĒ = VIL	Min	_	_	_	-	-	-	ns
		to Output Delay		Max	100	120	150	200	250	300	110
tgLQV	toe	Output Enable to	CE = VIL	Min	-	-	-	-	-	1	
		Output Delay		Max	50	50	65	75	100	100	ns
tehqz tghqz	tor	Chip Enable HIGH or Output Enable HIGH, whichever		Min	0	0	0	0	0	0	ns
		comes first, to Output Float (Note 2)	Max	40	40	50	60	60	60	113	
taxqx	toн	Output Hold from Addresses, CE, or	-	Min	0	0	0	0	0	0	
		OE, whichever occurred first		Max	_	-	-	-	-	-	ns

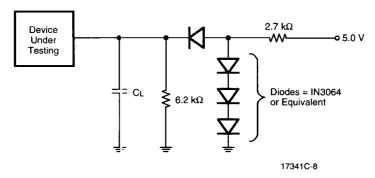
Notes:

- 1. Vcc must be applied simultaneously or before VPP, and removed simultaneously or after VPP.
- 2. This parameter is only sampled and not 100% tested.
- 3. Caution: The Am27LV010 must not be removed from, o. inserted into, a socket when VPP or VCC is applied.
- 4. Output Load: 1 TTL gate and C_L = 100 pF

Input Rise and Fall Times: 20 ns Input Pulse Levels: 0.40 V to 2.4 V

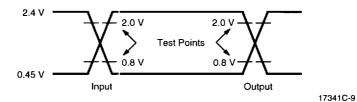
Timing Measurement Reference Level: 0.8 V and 2.0 V inputs and outputs

SWITCHING TEST CIRCUIT



C_L = 100 pF including jig capacitance

SWITCHING TEST WAVEFORM



AC Testing: Inputs are driven at 2.4 V for a Log c "1" and 0.45 V for a Logic "0". Input pulse rise and fall times are ≤ 20 ns.

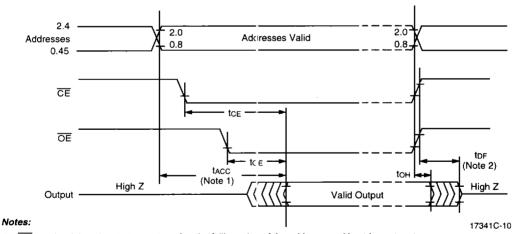


KEY TO SWITCHING WAVEFORMS

WAVEFORM	INPUTS	OUTPUTS		
	Must Be Steady	Will Be Steady		
	May Change from H to L	Will Be Changing from H to L		
	May Change from L to H	Will Be Changing from L to H		
	Dc n't Care, Ar y Change Pεrmitted	Changing, State Unknown		
>>	Dces Not Apply	Center Line is High Impedance "Off" State		

KS000010

SWITCHING WAVEFORM



- 1. \overline{OE} may be delayed up to t_{ACC} t_{OE} after the falling edge of the addresses without impact on t_{ACC}.
- 2. t_{DF} is specified from \overline{OE} or \overline{CE} , whichever occurs first.